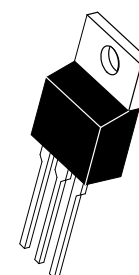
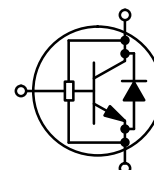


MJE18604D2

POWER TRANSISTORS
3 AMPERES
1600 VOLTS
100 WATTS



CASE 221A-06
TO-220AB

Advance Information

High Speed, High Gain Bipolar NPN Power Transistor with Integrated Collector-Emitter Diode and Built-in Efficient Antisaturation Network for 1600 V Applications

The MJE18604D2 is state-of-art High Speed High gain BIPolar transistor (H2BIP). Tight dynamic characteristics and lot to lot low spread (± 150 ns on storage time) make it ideally suitable for light ballast applications. Therefore, there is no more a need to guarantee an h_{fe} window.

Main features:

- Low Base Drive Requirement
- High DC Current Gain (30 Typical) @ $I_C = 400$ mA
- Extremely Low Storage Time Min/Max Guarantees Due to the Internal Active Antisaturation (H2BIP) Structure which Minimizes the Spread
- Integrated Collector-Emitter Free Wheeling Diode Matched with the Power Transistor
- Fully Characterized and Guaranteed Dynamic $V_{CE(sat)}$
- "6 Sigma" Process Providing Tight and Reproducible Parameter Spreads

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	V_{CEO}	800	Vdc
Collector-Emitter Sustaining Voltage @ $R = 200 \Omega$	V_{CER}	800	Vdc
Collector-Base Breakdown Voltage	V_{CBO}	1600	Vdc
Collector-Emitter Breakdown Voltage	V_{CES}	1600	Vdc
Emitter-Base Voltage	V_{EBO}	12	Vdc
Collector Current — Continuous	I_C	3	Adc
— Peak (1)	I_{CM}	8	
Base Current — Continuous	I_B	2	Adc
— Peak (1)	I_{BM}	4	
*Total Device Dissipation @ $T_C = 25^\circ C$	P_D	100	Watt
*Derate above $25^\circ C$		0.8	W/ $^\circ C$
Operating and Storage Temperature	T_J, T_{stg}	-65 to 150	$^\circ C$

THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case	$R_{\theta JC}$	1.25	$^\circ C/W$
— Junction to Ambient	$R_{\theta JA}$	62.5	
Maximum Lead Temperature for Soldering Purposes: 1/8" from case for 5 seconds	T_L	260	$^\circ C$

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle $\leq 10\%$.

This document contains information on a new product. Specifications and information herein are subject to change without notice.

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MJE18604D2
ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage ($I_C = 100\text{ mA}$, $L = 25\text{ mH}$, $R_{BE} = 200\ \Omega$)	$V_{CER(sus)}$	800			Vdc
Collector–Base Breakdown Voltage ($I_{CBO} = 1\text{ mA}$)	V_{CBO}	1600			Vdc
Emitter–Base Breakdown Voltage ($I_{EBO} = 1\text{ mA}$)	V_{EBO}	12	14		Vdc
Collector Cutoff Current ($V_{CBO} = \text{Rated } V_{CBO}$, $I_B = 0$)	I_{CBO}			100	μAdc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CES}$, $V_{EB} = 0$) ($V_{CE} = 1300\text{ V}$, $V_{EB} = 0$)	I_{CES}			100 1000 100	μAdc
Emitter–Cutoff Current ($V_{EB} = 11\text{ Vdc}$, $I_C = 0$)	I_{EBO}			500	μAdc

ON CHARACTERISTICS

Base–Emitter Saturation Voltage ($I_C = 0.5\text{ Adc}$, $I_B = 0.1\text{ Adc}$) ($I_C = 1\text{ Adc}$, $I_B = 0.1\text{ Adc}$) ($I_C = 2\text{ Adc}$, $I_B = 0.4\text{ Adc}$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	$V_{BE(sat)}$		0.8 0.6	1.1 1	Vdc
	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$			0.8 1	1 1	
	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$			0.9 0.8	1.2 1.1	
Collector–Emitter Saturation Voltage ($I_C = 250\text{ mAdc}$, $I_B = 25\text{ mAdc}$) ($I_C = 0.5\text{ Adc}$, $I_B = 50\text{ mAdc}$) ($I_C = 0.8\text{ Adc}$, $I_B = 80\text{ mAdc}$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	$V_{CE(sat)}$		1 1.7	1.25	Vdc
	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$			2.1 4	2.4	
	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$			3.7 5	5	
DC Current Gain ($I_C = 0.4\text{ Adc}$, $V_{CE} = 3\text{ Vdc}$) ($I_C = 5\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	h_{FE}	20 6	10	40	—
	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$		20 20	35 55		

DYNAMIC SATURATION VOLTAGE

Dynamic Saturation Voltage: Determined 1 μs and 3 μs respectively after rising I_{B1} reaches 90% of final I_{B1}	$I_C = 0.3\text{ Adc}$ $I_{B1} = 50\text{ mA}$ $V_{CC} = 300\text{ V}$	@ 1 μs	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	$V_{CE(dsat)}$		4.7 9.3	V
		@ 3 μs	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$			2.6 5.4	
	$I_C = 0.5\text{ Adc}$ $I_{B1} = 50\text{ mA}$ $V_{CC} = 300\text{ V}$	@ 1 μs	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$			9.7 18	
		@ 3 μs	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$			6.4 12.3	

DIODE CHARACTERISTICS

Forward Diode Voltage ($I_{EC} = 0.4\text{ Adc}$) ($I_{EC} = 1\text{ Adc}$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	V_{EC}		0.9 0.6	1.2	V
	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$			1.05 0.7	1.5	
Forward Recovery Time ($I_F = 0.4\text{ Adc}$, $di/dt = 10\text{ A}/\mu\text{s}$) ($I_F = 1.0\text{ Adc}$, $di/dt = 10\text{ A}/\mu\text{s}$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_{fr}		0.9 1.5		μs
	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$			1.15 1.6		

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS					
Current Gain Bandwidth ($I_C = 0.5 \text{ Adc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1 \text{ MHz}$)	f_T		13		MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 1 \text{ MHz}$)	C_{ob}		230	500	pF
Input Capacitance ($V_{CE} = 8 \text{ Vdc}$)	C_{ib}		480	1000	pF

SWITCHING CHARACTERISTICS: Resistive Load (D.C. $\leq 10\%$, Pulse Width = $40 \mu\text{s}$)

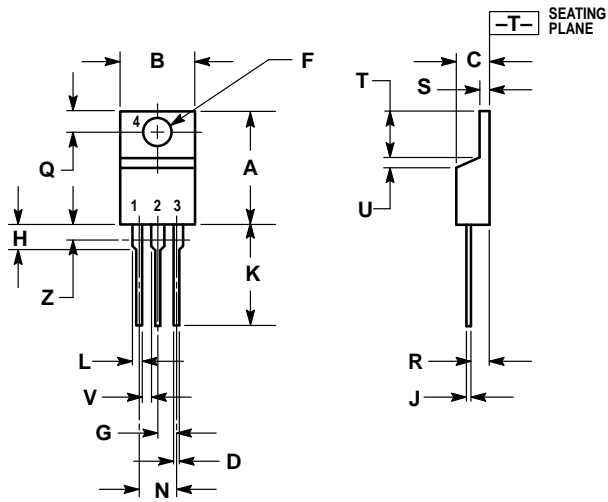
Delay Time	$I_C = 0.5 \text{ Adc}$ $I_{B1} = 66 \text{ mAdc}$ $I_{B2} = 390 \text{ mAdc}$ $V_{CC} = 125 \text{ V}$	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_d		95 110	150	ns	
Rise Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_r		475 900	750	ns	
Storage Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_s	400		910	700	ns
Fall Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_f			675 775	850	ns
Turn-on Time	$I_C = 0.3 \text{ Adc}$ $I_{B1} = 50 \text{ mAdc}$ $I_{B2} = 50 \text{ mAdc}$ $V_{CC} = 125 \text{ V}$	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_{on}		440 570		ns	
Storage Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_s		4 5.9		μs	
Fall Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_f			375 675		ns
Turn-off Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_{off}			4.5 6.6		μs
Turn-on Time	$I_C = 0.3 \text{ Adc}$ $I_{B1} = 50 \text{ mAdc}$ $I_{B2} = 150 \text{ mAdc}$ $V_{CC} = 125 \text{ V}$	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_{on}		465 550	600	ns	
Storage Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_s	500		1800	800	ns
Fall Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_f			800 550	1000	ns
Turn-off Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_{off}			1.5 2.4	1.75	μs
Turn-on Time	$I_C = 0.5 \text{ Adc}$ $I_{B1} = 50 \text{ mAdc}$ $I_{B2} = 50 \text{ mAdc}$ $V_{CC} = 125 \text{ V}$	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_{on}		550 1300		ns	
Storage Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_s			4.35 5		μs
Fall Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_f			500 2000		ns
Turn-off Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_{off}			4.8 7		μs
Delay Time	$I_C = 0.5 \text{ Adc}$ $I_{B1} = 50 \text{ mAdc}$ $I_{B2} = 250 \text{ mAdc}$ $V_{CC} = 125 \text{ V}$	@ $T_C = 25^\circ\text{C}$	t_d		100	300	ns	
Rise Time		@ $T_C = 25^\circ\text{C}$	t_r		300	800	ns	
Storage Time		@ $T_C = 25^\circ\text{C}$	t_s		1	1.2	μs	
Fall Time		@ $T_C = 25^\circ\text{C}$	t_f		200	350	ns	

MJE18604D2

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS: Inductive Load (V_{CC} = 15 V)					
Fall Time	I _C = 300 mA I _{B1} = 50 mA I _{B2} = 50 mA V _Z = 300 V L _C = 200 μH	@ T _C = 25°C @ T _C = 125°C	t _f	170 210	ns
Storage Time		@ T _C = 25°C @ T _C = 125°C	t _s	1.7 2.7	μs
Crossover Time		@ T _C = 25°C @ T _C = 125°C	t _c	150 400	ns
Fall Time	I _C = 300 mA I _{B1} = 50 mA I _{B2} = 150 mA V _Z = 300 V L _C = 200 μH	@ T _C = 25°C @ T _C = 125°C	t _f	160 150	250 ns
Storage Time		@ T _C = 25°C @ T _C = 125°C	t _s	0.7 1.1	1 μs
Crossover Time		@ T _C = 25°C @ T _C = 125°C	t _c	160 160	250 ns
Fall Time	I _C = 500 mA I _{B1} = 50 mA I _{B2} = 50 mA V _Z = 300 V L _C = 200 μH	@ T _C = 25°C @ T _C = 125°C	t _f	165 700	ns
Storage Time		@ T _C = 25°C @ T _C = 125°C	t _s	3 4.1	μs
Crossover Time		@ T _C = 25°C @ T _C = 125°C	t _c	200 800	ns
Fall Time	I _C = 500 mA I _{B1} = 50 mA I _{B2} = 250 mA V _Z = 300 V L _C = 200 μH	@ T _C = 25°C @ T _C = 125°C	t _f	110 130	175 ns
Storage Time		@ T _C = 25°C @ T _C = 125°C	t _s	0.7 1.8	1 μs
Crossover Time		@ T _C = 25°C @ T _C = 125°C	t _c	130 250	200 ns

PACKAGE DIMENSIONS




- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

- STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

CASE 221A-06
 TO-220AB
 ISSUE Y

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